Title: Memory programming of TiO_{2-x} films by Conductive Atomic Force Microscopy evidencing filamentary resistive switching

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Title:

Memory programming of TiO_{2-x} films by Conductive Atomic Force Microscopy evidencing filamentary resistive switching

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- We correlate RRAM performance with C-AFM measurements.
- We demonstrate resistive switching through C-AFM process.
- We present evidence of filament formation.
- We demonstrate resistive switching in nanoscale area.

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